



TO-92 Plastic-Encapsulate Transistors

2N6517 TRANSISTOR (NPN)

FEATURES

Power dissipation

$$P_{CM}: 0.625 \text{ W (Tamb=25}^\circ\text{C)}$$

Collector current

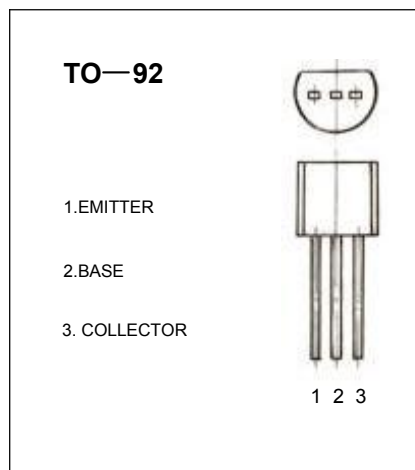
$$I_{CM}: 0.5 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: 350 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\text{mA}, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\text{mA}, I_C=0$	12			V
Collector cut-off current	I_{CBO}	$V_{CB}=30\text{V}, I_E=0$			5	μA
Collector cut-off current	I_{EBO}	$V_{EB}=25\text{V}, I_C=0$			1	μA
Emitter cut-off current	$H_{FE(1)}$	$V_{CE}=10\text{V}, I_C=0\text{mA}$			50	μA
DC current gain	$H_{FE(2)}$	$V_{CE}=5\text{V}, I_C=10\text{mA}$	20		200	
DC current gain	$H_{FE(3)}$	$V_{CE}=5\text{V}, I_C=100\text{mA}$	30		300	
DC current gain	$H_{FE(4)}$	$V_{CE}=5\text{V}, I_C=500\text{mA}$	20		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50\text{mA}, I_B=0.5\text{mA}$			1.5	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{mA}, I_B=0.5\text{mA}$			1.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=500\text{mA}, I_B=0.5\text{mA}$			2.0	V
Base-emitter voltage	V_{BE}	$V_{CE}=50\text{V}, I_C=5\text{mA}$			1.75	V

CLASSIFICATION OF HFE

Rank	1	2	3
Range	20-100	100-200	200-300

